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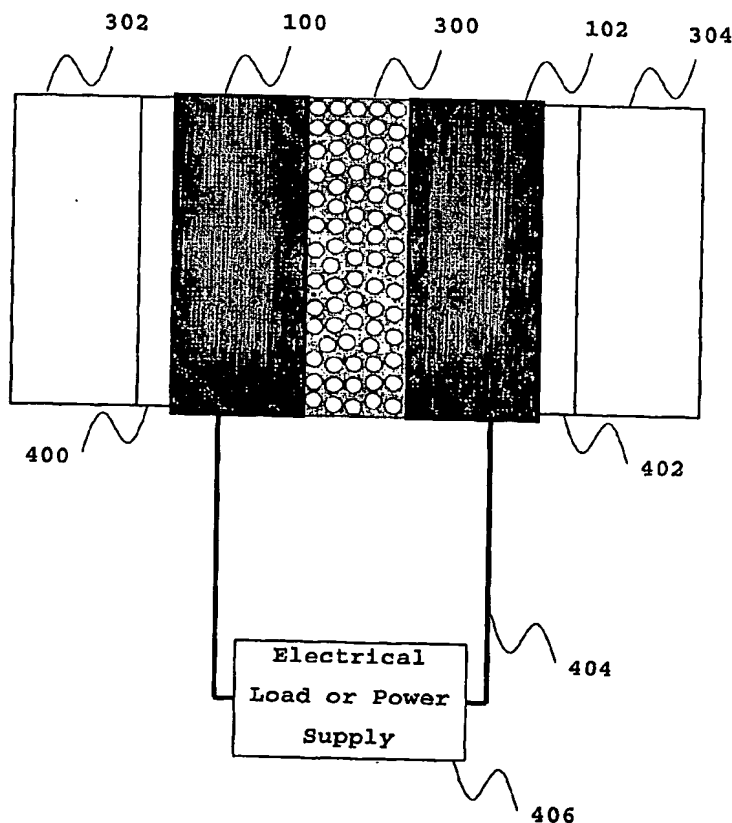
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(54) Title: MULTIPLE TUNNEL JUNCTION THERMOTUNNEL DEVICE ON THE BASIS OF BALLISTIC



(57) Abstract: The present invention is a tunnel diode, in which the space between the emitter electrode and the collector electrode is occupied by a porous material which has a thickness less than the free mean free path of an electron in the porous material. The present invention also includes heat pumping and power generation devices comprising the tunnel diode.

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